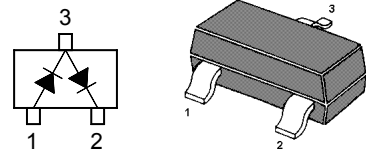


BAV99

Silicon Epitaxial Planar Switching Diode

Fast switching in thick and thin-film circuits diode



Marking Code: A7
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current (Double Diode Loaded)	I_F	125	mA
Continuous Forward Current (Single Diode Loaded)	I_F	215	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$ 0.5	A
		at $t = 1\text{ ms}$ 1	
		at $t = 1\text{ }\mu\text{s}$ 4.5	
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit			
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	0.715 0.855 1 1.25	V			
Reverse Current at $V_R = 25\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}, T_j = 150\text{ }^\circ\text{C}$ at $V_R = 75\text{ V}, T_j = 150\text{ }^\circ\text{C}$		I_R		30 1 30 50	nA μA μA μA	
Diode Capacitance at $V_R = 0, f = 1\text{ MHz}$				C_d	1.5	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}, I_R = 1\text{ mA}, R_L = 100\text{ }\Omega$				t_{rr}	4	ns

TOP DYNAMIC



ISO14001 : 2004 Certificate No. 121505007
ISO 9001 : 2008 Certificate No. 50114012
OHSAS 18001 : 2007 Certificate No. 05131508008
IECQ QC 080000 Certificate No. 8224100074102

Dated : 15/06/2012

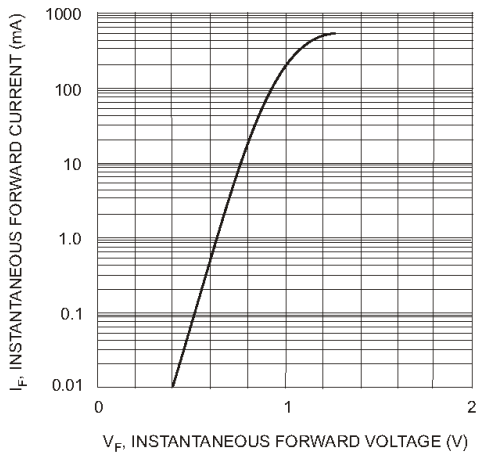


Fig. 1 Forward Characteristics

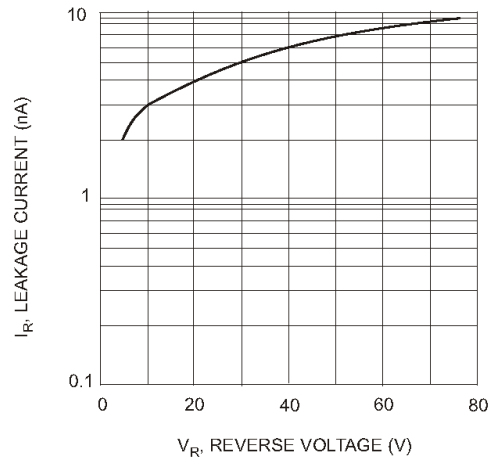


Fig. 2 Typical Leakage Current vs Reverse Voltage

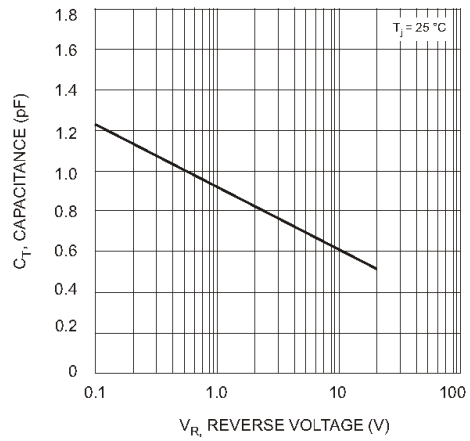


Fig. 3 Typical Total Capacitance vs Reverse Voltage